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INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

(use as many sheets as necessary)

				Complete If Known
Application Number				10/667,615
Filing Date				09/22/03
First Named Inventor				Theodore W. Houston
Group Art Unit				2811
Examiner Name				Douglas W. Owens
Sheet	1	of	1	Attorney Docket No. TI-35657

## U.S. PATENT DOCUMENTS

Exam. Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
AA	6,396,108			Krivokapic et al.	5/28/02	
AB	6,307,230			Chatterjee et al.	10/23/01	
AC	6,225,175			Houston	5/1/01	
AD						
AE						
AF						
AG						
AH						
AI						
AJ						
AK						
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## FOREIGN PATENT DOCUMENTS

Exam. Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>2</sup> (if known)				
BA	WO	02/103703	A2		Innovative Silicon SA	12/27/02		
BB								
BC								
BD								
BE								
BF								
BG								

## OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Exam. Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
CA	KAZUMI INOH, ET AL., "FBC (Floating Body Cell) for Embedded DRAM on SOI" 2003 Symposium on VLSI Technology Digest of Technical Papers, pp. 1-2		
CB	TAKASHI OHSAWA, ET AL., "A Memory Using One-Transistor Gain Cell on SOI (FBC) with Performance Suitable for Embedded DRAM's" 2003 Symposium on VLSI Circuits Digest of Technical Papers, pp. 1-4		
CC	B. DOYLE, ET AL., "Tri-Gate Fully-Depleted CMOS Transistors: Fabrication, Design and Layout" 2003 Symposium on VLSI Technology Digest of Technical Papers, pp. 1-2		
CD			
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CF			
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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